

# 2SC3440

FOR HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

2SC3440 is a super mini silicon NPN epitaxial transistor designed with high collector current, small VCE(sat).

Complementary with 2SA1365.

## FEATURE

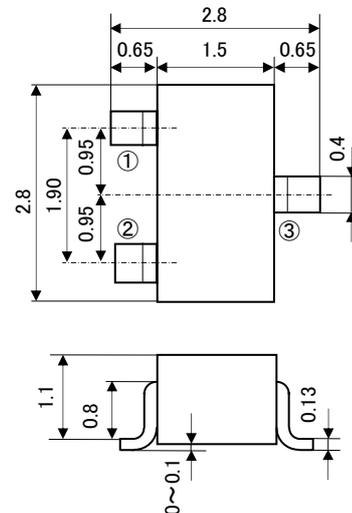
- Low collector to emitter saturation voltage  
VCE(sat)=0.2V typ
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting
- High collector current ICM=1000mA
- High gain band with product fT=180MHz typ

## APPLICATION

Small type motor drive, relay drive, power supply

## OUTLINE DRAWING

Unit: mm



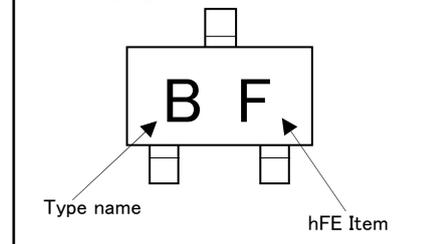
## TERMINAL CONNECTER

- ①: BASE JEITA: SC-59
- ②: EMITTER JEDEC: Similar to TO-236
- ③: COLLECTOR

## MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base voltage	V <sub>CBO</sub>	25	V
Emitter to Base voltage	V <sub>EBO</sub>	4	V
Collector to Emitter voltage	V <sub>CEO</sub>	20	V
Collector current	I <sub>C</sub>	700	mA
Peak collector current	I <sub>CM</sub>	1000	mA
Collector dissipation	P <sub>c</sub>	200	mW
Junction temperature	T <sub>j</sub>	+150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to B breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> =10 μA, I <sub>E</sub> =0mA	25	-	-	V
E to B breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> =10 μA, I <sub>C</sub> =0mA	4	-	-	V
C to E breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =100 μA, R <sub>BE</sub> =∞	20	-	-	V
Collector cut off current	I <sub>CBO</sub>	V <sub>CB</sub> =25V, I <sub>E</sub> =0mA	-	-	1	μA
Emitter cut off current	I <sub>EBO</sub>	V <sub>EB</sub> =2V, I <sub>C</sub> =0mA	-	-	1	μA
DC forward current gain *	hFE	V <sub>CE</sub> =4V, I <sub>C</sub> =100mA	150	-	800	-
C to E Saturation Voltage	VCE(sat)	I <sub>C</sub> =500mA, I <sub>B</sub> =25mA	-	0.2	0.5	V
Gain bandwidth product	fT	V <sub>CE</sub> =6V, I <sub>E</sub> =-10mA	-	180	-	MHz

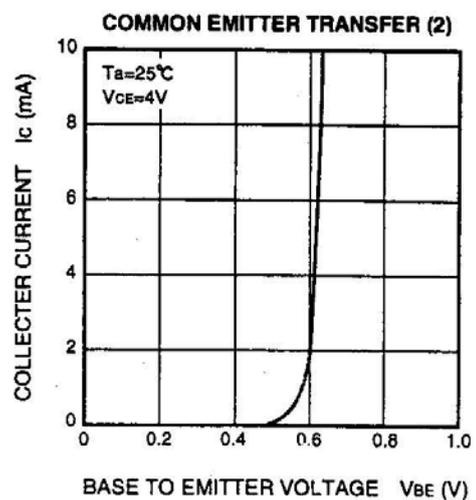
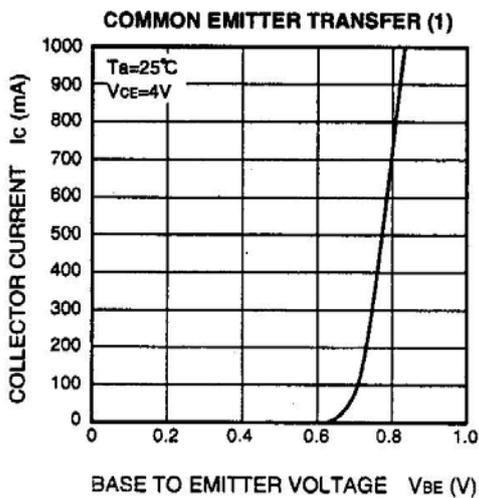
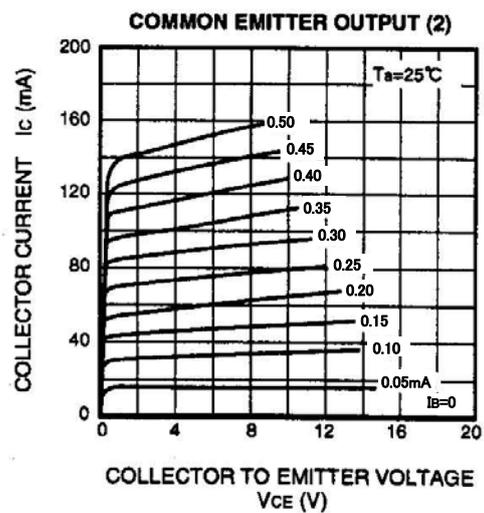
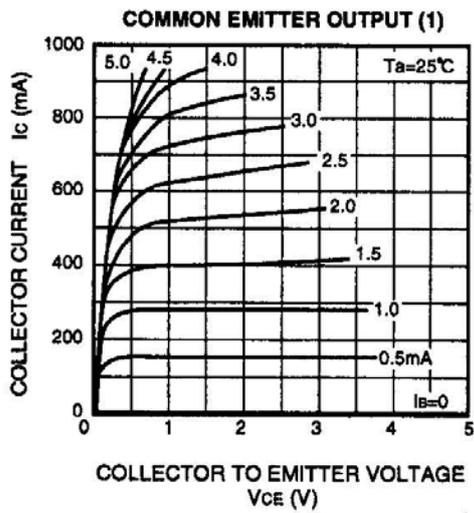
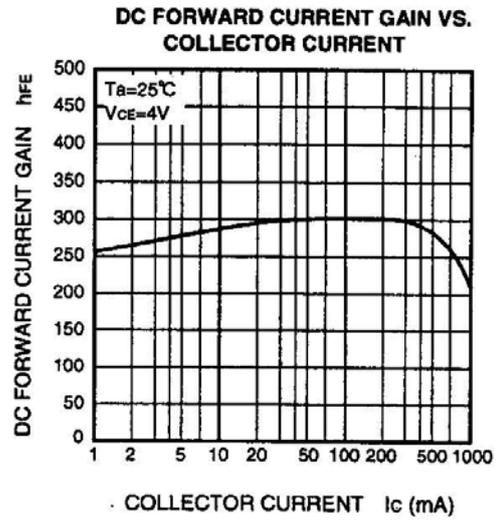
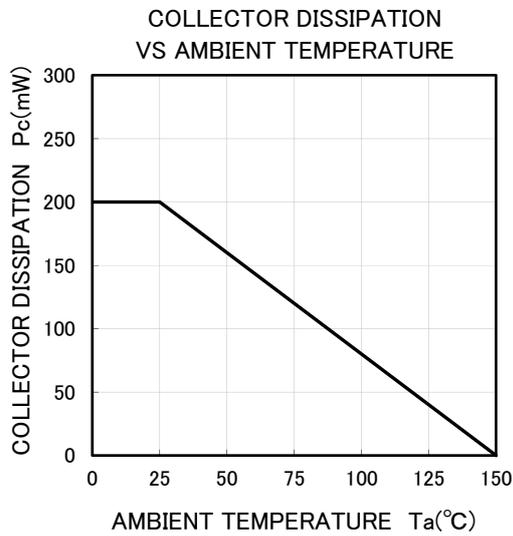
※: It shows hFE classification at right table.

Item	E	F	G
hFE	150~300	250~500	400~800

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## TYPICAL CHARACTERISTICS





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